SILICON N-CHANNEL RF POWER MOSFET

DESCRIPTION:

The **TPV596** is Designed for Common Source Push Pull RF Power Applications up to 400 MHz.

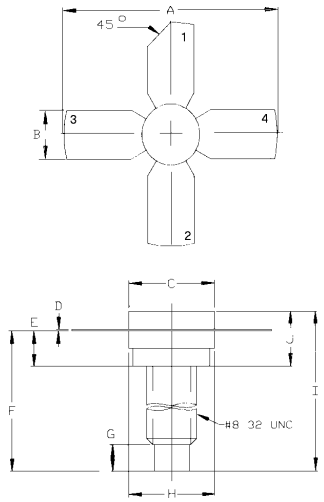
FEATURES:

- P_G = 12 dB min. at 0.5 W/ 860 MHz
- Common Emitter
- ***Omnigold***™ Metallization System

MAXIMUM RATINGS

I_C	0.7 A
V_{CE}	24 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
P_{DISS}	8.75 W @ T_C = 25 °C

PACKAGE STYLE 280 4L STUD



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25,65	1.055/26,80
B	.220/5,59	.230/5,84
C	.270/6,86	.285/7,24
D	.003/0,08	.007/0,18
E	.117/2,97	.137/3,48
F	.572/14,53	
G	.130/3.30	
H	.275/6,99	.285/7,24
I	.640/16,26	
J	.175/4,45	.215/5,51

1 = COLLECTOR 2 = BASE 3 & 4 = EMITTER

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 20 mA	24			V
BV_{CBO}	I_C = 1.0 mA	45			V
BV_{CER}	I_C = 20 mA R_{BE} = 10 Ω	50			V
BV_{EBO}	I_E = 0.25 mA	3.5			V
I_{CBO}	V_{CB} = 28 V			0.45	mA
h_{FE}	I_C = 100 mA V_{CE} = 5.0 V	15		120	---
C_{OB}	V_{CB} = 28 V f = 1.0 MHz			5.0	pF
P_G	V_{CE} = 20 V I_E = 0.22 A f = 860 MHz	11.5	12		dB

Specifications are subject to change without notice.